

**isc N-Channel MOSFET Transistor**
**IQTQ60N10T**
**• FEATURES**

- Drain Source Voltage-  
:  $V_{DSS} = 200V(\text{Min})$
- Static Drain-Source On-Resistance  
:  $R_{DS(on)} = 40m\Omega (\text{Max})$
- Fast Switching
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

**• APPLICATIONS**

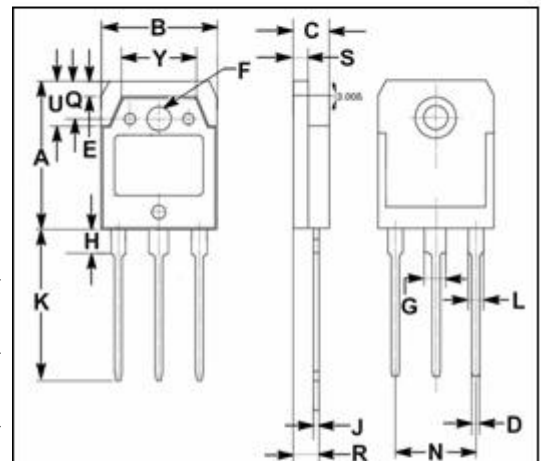
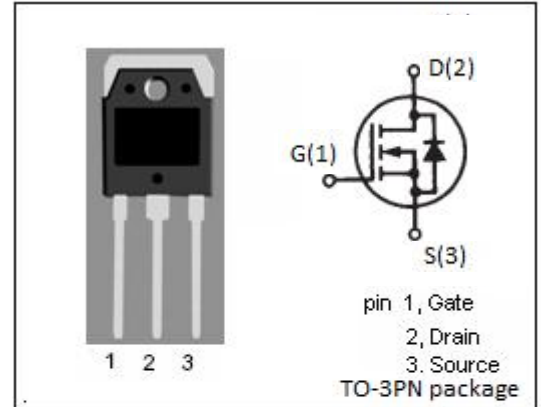
- Switch-Mode and Resonant-Mode Power Supplies
- DC-DC Converters
- AC and DC Motor Drives
- Robotics and Servo Controls

**• ABSOLUTE MAXIMUM RATINGS( $T_a=25^\circ\text{C}$ )**

SYMBOL	PARAMETER	VALUE	UNIT
$V_{DSS}$	Drain-Source Voltage	200	V
$V_{GS}$	Gate-Source Voltage-Continuous	$\pm 20$	V
$I_D$	Drain Current-Continuous	60	A
$I_{DM}$	Drain Current-Single Plused	150	A
$P_D$	Total Dissipation @ $T_c=25^\circ\text{C}$	500	W
$T_j$	Max. Operating Junction Temperature	-55~175	$^\circ\text{C}$
$T_{stg}$	Storage Temperature	-55~175	$^\circ\text{C}$

**• THERMAL CHARACTERISTICS**

SYMBOL	PARAMETER	MAX	UNIT
$R_{th-j-c}$	Thermal Resistance, Junction to Case	0.30	$^\circ\text{C/W}$



DIM	mm	
	MIN	MAX
A	19.60	20.30
B	15.50	15.70
C	4.70	4.90
D	0.90	1.10
E	1.90	2.10
F	3.40	3.60
G	2.90	3.20
H	3.20	3.40
J	0.595	0.605
K	19.80	20.70
L	1.90	2.20
N	10.89	10.91
Q	4.90	5.10
R	3.35	3.45
S	1.995	2.100
U	5.90	6.20
Y	9.90	10.10

## isc N-Channel MOSFET Transistor

## IXTQ60N10T

## • ELECTRICAL CHARACTERISTICS

T<sub>c</sub>=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYPE	MAX	UNIT
V <sub>(BR)DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> = 0; I <sub>D</sub> =250μA	200			V
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> = V <sub>GS</sub> ; I <sub>D</sub> =250uA	3		5	V
R <sub>DS(on)</sub>	Drain-Source On-Resistance	V <sub>GS</sub> = 10V; I <sub>D</sub> = 30A			40	mΩ
I <sub>GSS</sub>	Gate-Body Leakage Current	V <sub>GS</sub> = ±20V; V <sub>DS</sub> = 0			±200	nA
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> =200V; V <sub>GS</sub> = 0 V <sub>DS</sub> =200V; V <sub>GS</sub> = 0; T <sub>J</sub> =150°C			1 250	μA
V <sub>SD</sub>	Diode Forward On-voltage	I <sub>F</sub> = 60A; V <sub>GS</sub> = 0			1.3	V

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